

Application No. 10/622,614
Amendment dated December 23, 2004
Reply to Office Action of July 26, 2004

AMENDMENTS TO THE SPECIFICATION:

Please amend the specification as follows:

Amendments To The Title:

Amend the title to read as follows:

SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME FOR
PREVENTING DEFECTIVE FILLING OF INTERCONNECTION AND CRACKING
OF INSULATING FILM

Amendments To Abstract:

Amend the abstract on page 75 to read as follows:

The semiconductor device ~~comprises:~~ has insulating films 40, 42 formed over a substrate 10; an interconnection 58 buried in at least a surface side of the insulating films 40, 42; insulating films 60, 62 formed on the insulating film 42 and including a hole-shaped via-hole 60 and a groove-shaped via-hole 66a having a pattern bent at a right angle; and buried conductors 70, 72a buried in the hole-shaped via-hole 60 and the groove-shaped via-hole 66a, ~~wherein the~~ A groove-shaped via-hole 66a is formed to have a width which is smaller than a width of the hole-shaped via-hole 66. ~~Whereby, the defective~~ Defective filling of the buried conductor is ~~prevented~~, and the cracking of the inter-layer insulating film can be prevented. Steps on the

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conductor plug can be reduced, ~~so that the step cannot be influential on the upper interconnection layers and insulating layers.~~ Accordingly, defective contact with the upper interconnection layer and the problems taking place in forming films can be prevented, ~~and resultantly the semiconductor device can have high water resistance and high interconnection reliability.~~